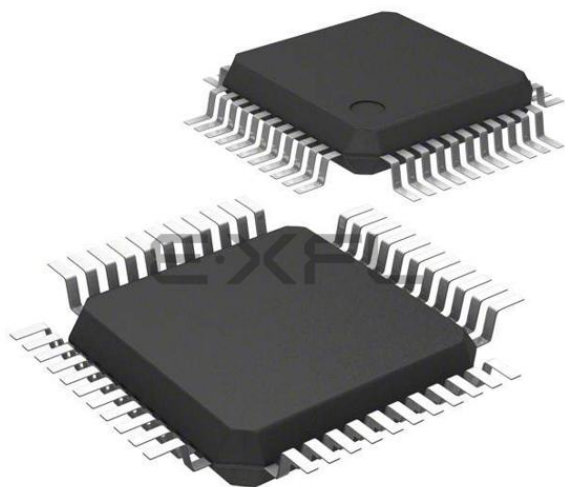




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fhafp-30

(2/5)

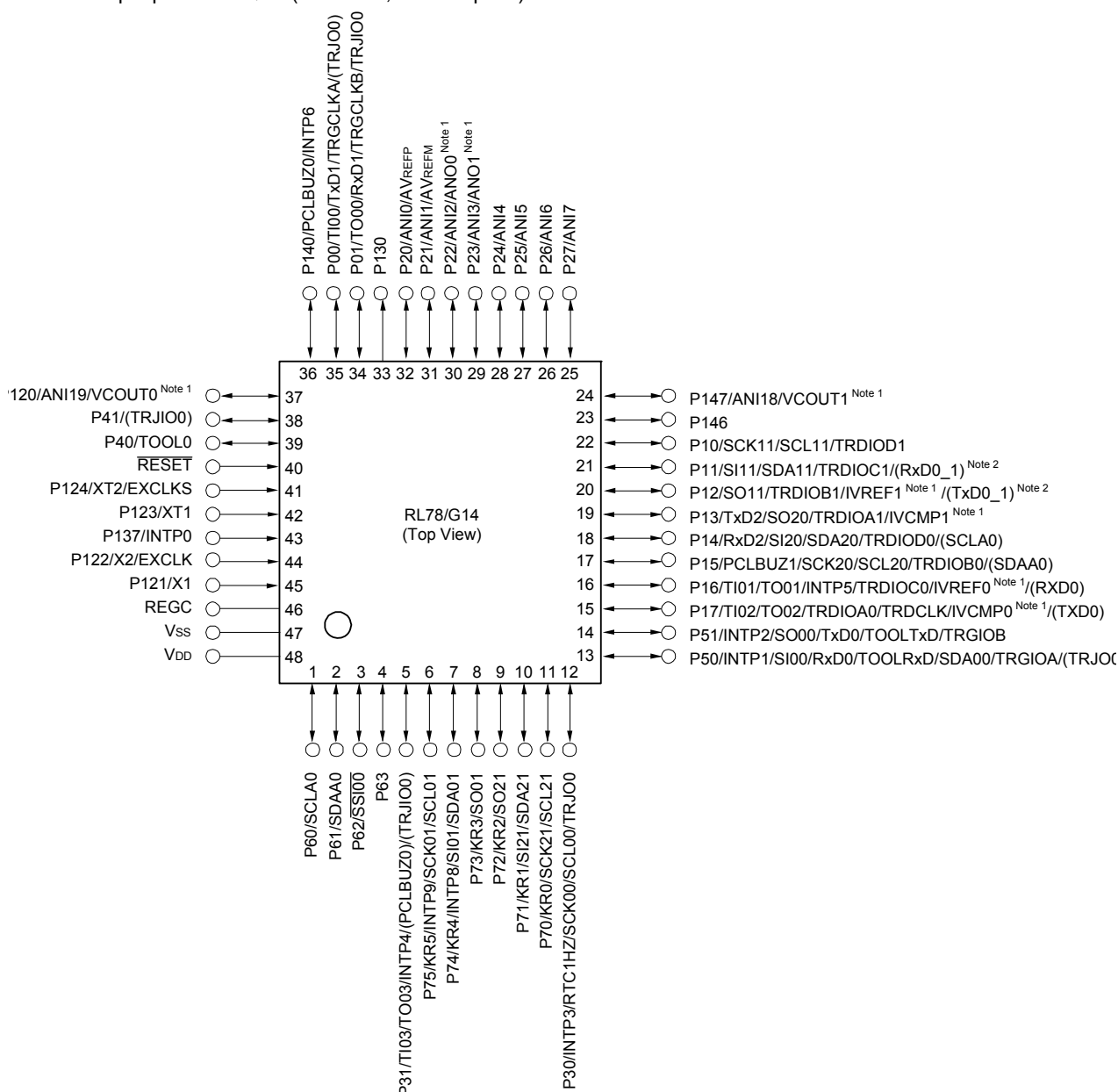
Pin count	Package	Fields of Application Note	Ordering Part Number
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	A	R5F104EAANA#U0, R5F104ECANA#U0, R5F104EDANA#U0, R5F104EEANA#U0, R5F104EFANA#U0, R5F104EGANA#U0, R5F104EHANA#U0 R5F104EAANA#W0, R5F104ECANA#W0, R5F104EDANA#W0, R5F104EEANA#W0, R5F104EFANA#W0, R5F104EGANA#W0, R5F104EHANA#W0
		D	R5F104EADNA#U0, R5F104ECDNA#U0, R5F104EDDNA#U0, R5F104EEDNA#U0, R5F104EFDNA#U0, R5F104EGDNA#U0, R5F104EHDNA#U0 R5F104EADNA#W0, R5F104ECDNA#W0, R5F104EDDNA#W0, R5F104EEDNA#W0, R5F104EFDNA#W0, R5F104EGDNA#W0, R5F104EHDNA#W0
		G	R5F104EAGNA#U0, R5F104ECGNA#U0, R5F104EDGNA#U0, R5F104EEGNA#U0, R5F104EFGNA#U0, R5F104EGGNA#U0, R5F104EHGNA#U0 R5F104EAGNA#W0, R5F104ECGNA#W0, R5F104EDGNA#W0, R5F104EEGNA#W0, R5F104EFGNA#W0, R5F104EGGNA#W0, R5F104EHGNA#W0
44 pins	44-pin plastic LQFP (10 × 10, 0.8 mm pitch)	A	R5F104FAAFP#V0, R5F104FCAFP#V0, R5F104FDAFP#V0, R5F104FEAFP#V0, R5F104FFAFP#V0, R5F104FGAFP#V0, R5F104FHAFP#V0, R5F104FJAFP#V0 R5F104FAAFP#X0, R5F104FCAFP#X0, R5F104FDAFP#X0, R5F104FEAFP#X0, R5F104FFAFP#X0, R5F104FGAFP#X0, R5F104FHAFP#X0, R5F104FJAFP#X0
		D	R5F104FADFP#V0, R5F104FCDFP#V0, R5F104FDDFP#V0, R5F104FEDFP#V0, R5F104FFDFP#V0, R5F104FGDFP#V0, R5F104FHDFP#V0, R5F104FJDFP#V0 R5F104FADFP#X0, R5F104FCDFP#X0, R5F104FDDFP#X0, R5F104FEDFP#X0, R5F104FFDFP#X0, R5F104FGDFP#X0, R5F104FHDFP#X0, R5F104FJDFP#X0
		G	R5F104FAGFP#V0, R5F104FCGFP#V0, R5F104FDGFP#V0, R5F104FEGFP#V0, R5F104FFGFP#V0, R5F104FGGFP#V0, R5F104FHGFP#V0, R5F104FJGFP#V0 R5F104FAGFP#X0, R5F104FCGFP#X0, R5F104FDGFP#X0, R5F104FEGFP#X0, R5F104FFGFP#X0, R5F104FGGFP#X0, R5F104FHGFP#X0, R5F104FJGFP#X0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.6 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

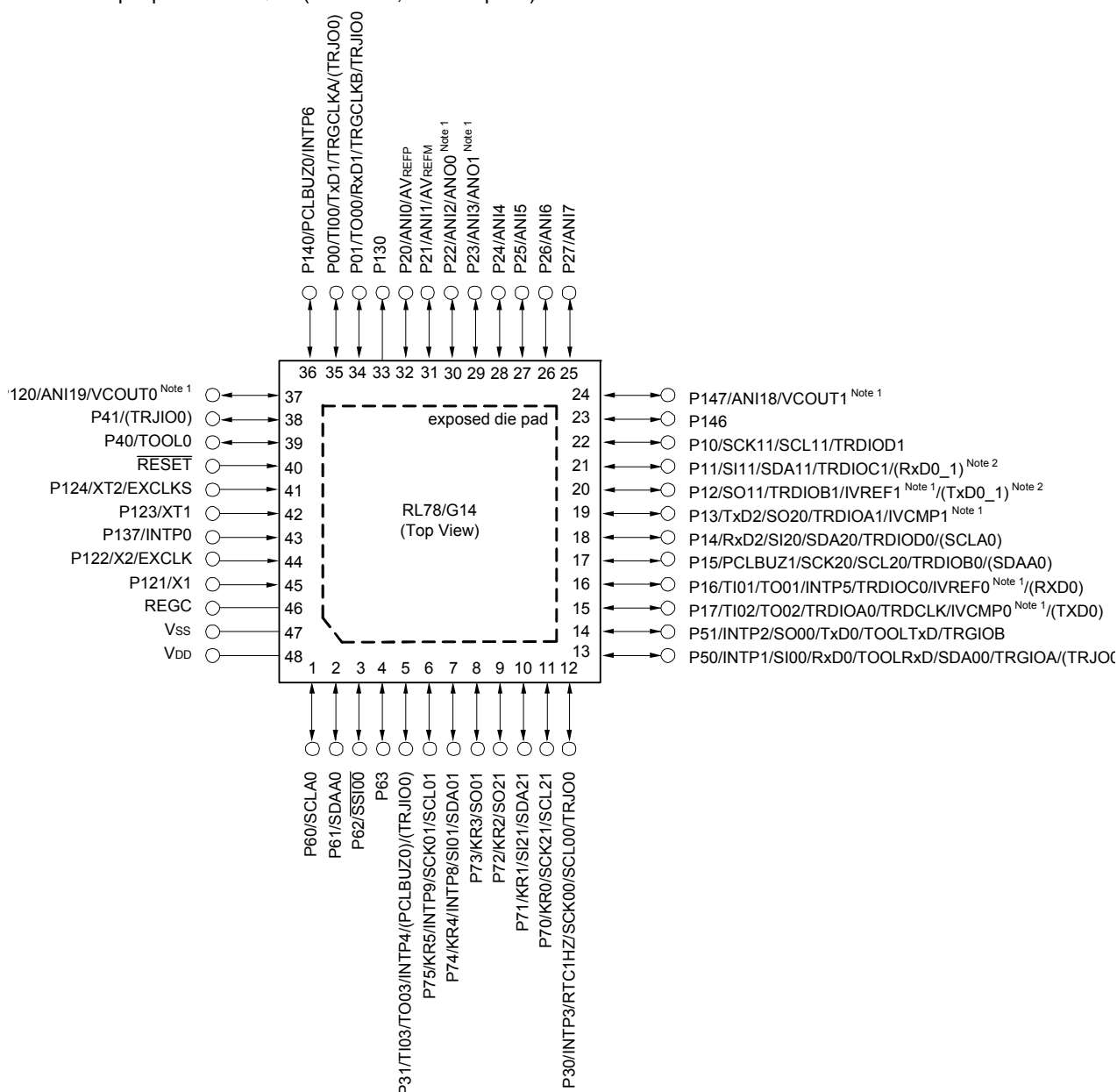
Note 2. Mounted on the 384 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

- 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

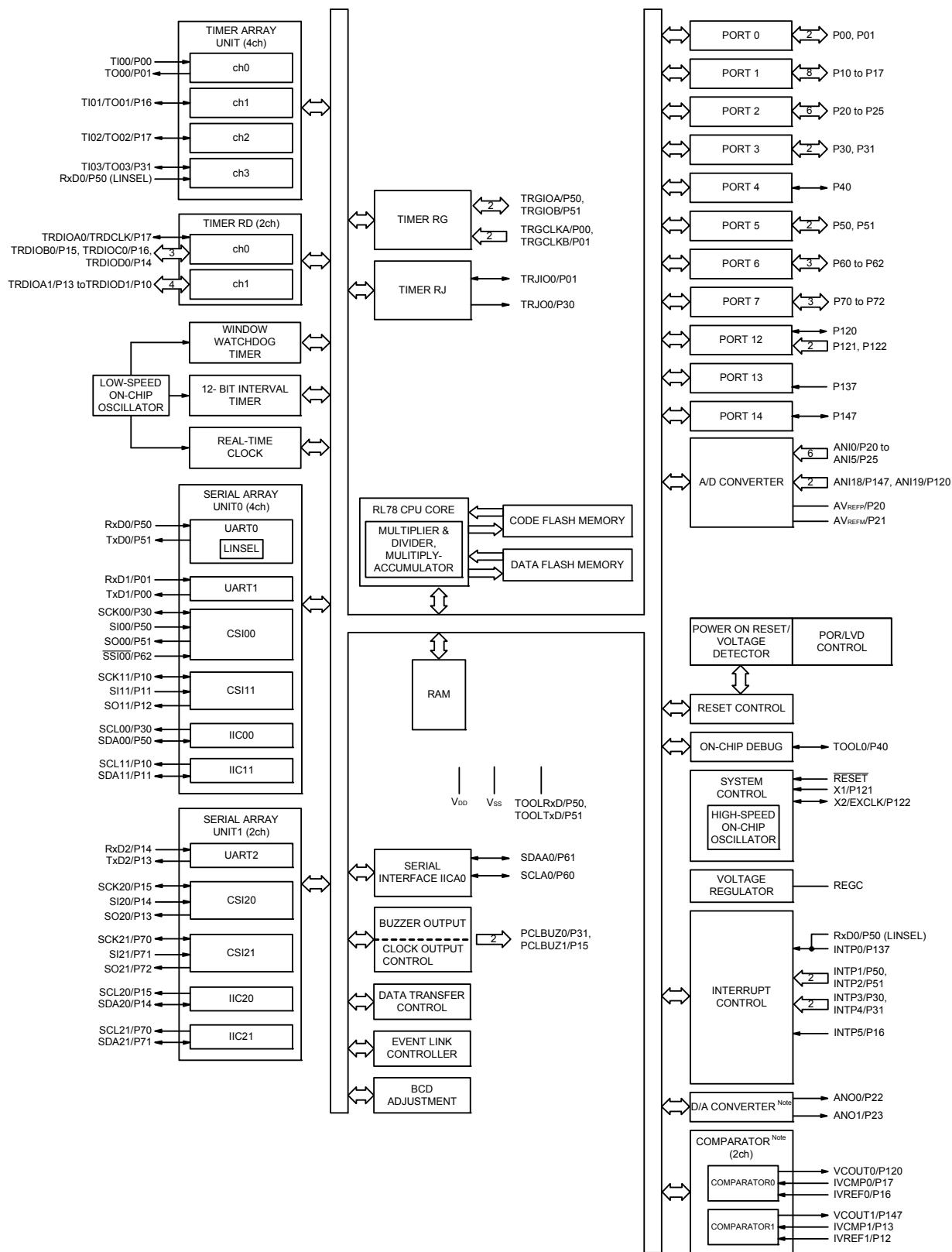
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

Remark 3. It is recommended to connect an exposed die pad to Vss.

1.5.3 36-pin products



Note Mounted on the 96 KB or more code flash memory products.

[80-pin, 100-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		80-pin	100-pin
		R5F104Mx (x = K, L)	R5F104Px (x = K, L)
Code flash memory (KB)		384 to 512	384 to 512
Data flash memory (KB)		8	8
RAM (KB)		32 to 48 Note	32 to 48 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)	
	High-speed on-chip oscillator clock (f _{IH})	HS (high-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V _{DD} = 1.6 to 5.5 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f _{IH} = 32 MHz operation)	
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)	
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)	

Note In the case of the 48 KB, this is about 47 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

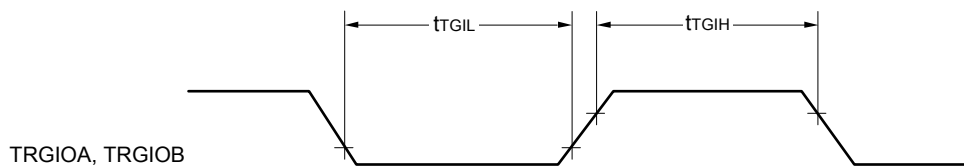
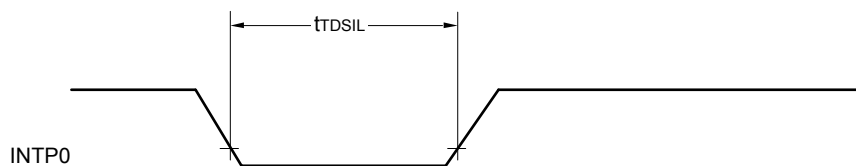
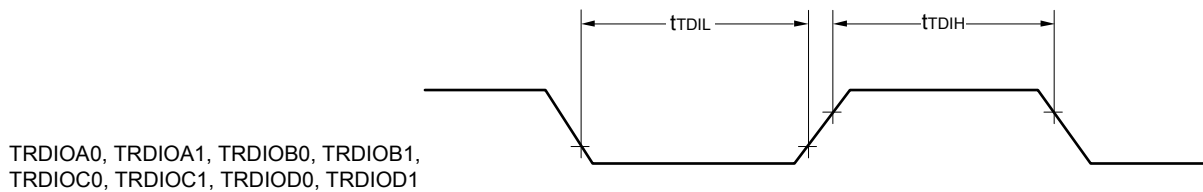
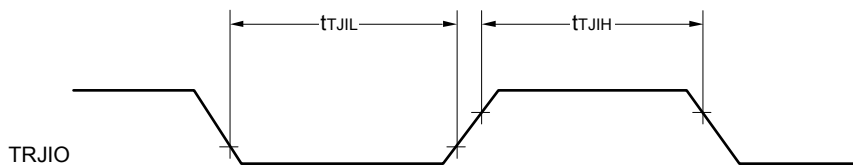
- Note 1.** Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or VSS, EVSS0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
- | | |
|-----------------------------|-------------------------------------|
| HS (high-speed main) mode: | 2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz |
| | 2.4 V ≤ VDD ≤ 5.5 V@1 MHz to 16 MHz |
| LS (low-speed main) mode: | 1.8 V ≤ VDD ≤ 5.5 V@1 MHz to 8 MHz |
| LV (low-voltage main) mode: | 1.6 V ≤ VDD ≤ 5.5 V@1 MHz to 4 MHz |
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.6		mA
						V _{DD} = 3.0 V		2.6		
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.3		
						V _{DD} = 3.0 V		2.3		
			HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.4	10.2	mA
						V _{DD} = 3.0 V		5.4	10.2	
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.0	9.6	
						V _{DD} = 3.0 V		5.0	9.6	
				f _{HOCO} = 48 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.2	7.8	
						V _{DD} = 3.0 V		4.2	7.8	
				f _{HOCO} = 24 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.0	7.4	
						V _{DD} = 3.0 V		4.0	7.4	
				f _{HOCO} = 16 MHz, f _{IIH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.0	5.3	
						V _{DD} = 3.0 V		3.0	5.3	
			LS (low-speed main) mode Note 5	f _{HOCO} = 8 MHz, f _{IIH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.4	2.3	mA
						V _{DD} = 2.0 V		1.4	2.3	
			LV (low-voltage main) mode Note 5	f _{HOCO} = 4 MHz, f _{IIH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.9	mA
						V _{DD} = 2.0 V		1.3	1.9	
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.4	6.2	mA
						Resonator connection		3.6	6.4	
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.4	6.2	
						Resonator connection		3.6	6.4	
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.2	mA
						Resonator connection		1.2	2.3	
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.2	
						Resonator connection		1.2	2.3	
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		4.9	7.1	μA
						Resonator connection		4.9	7.1	
				f _{SUB} = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		4.9	7.1	
						Resonator connection		4.9	7.1	
				f _{SUB} = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		5.1	8.8	
						Resonator connection		5.1	8.8	
				f _{SUB} = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		5.5	10.5	
						Resonator connection		5.5	10.5	
				f _{SUB} = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		6.5	14.5	
						Resonator connection		6.5	14.5	

(Notes and Remarks are listed on the next page.)



- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +85°C, 2.4 V ≤ VDD ≤ 5.5 V, 1.6 V ≤ EVDD = EVDD1 ≤ VDD, VSS = EVSS0 = EVSS1 = 0 V, Reference voltage (+) = VBGR ^{Note 3}, Reference voltage (-) = AVREFM = 0 V ^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	tCONV	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±0.60	% FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Analog input voltage	VAIN			0		VBGR ^{Note 3}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = VSS, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147			8.5 Note 2	mA
		Per pin for P60 to P63			15.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EVDD0 ≤ 5.5 V		40.0	mA
			2.7 V ≤ EVDD0 < 4.0 V		15.0	mA
			2.4 V ≤ EVDD0 < 2.7 V		9.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EVDD0 ≤ 5.5 V		40.0	mA
			2.7 V ≤ EVDD0 < 4.0 V		35.0	mA
			2.4 V ≤ EVDD0 < 2.7 V		20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)			80.0	mA
	IOL2	Per pin for P20 to P27, P150 to P156			0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4 V ≤ VDD ≤ 5.5 V		5.0	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVSS0, EVSS1, and VSS pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IOL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IOL = 10.0 mA

$$\text{Total output current of pins} = (10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.4 AC Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Tcy	Main system clock (fMAIN) operation	HS (high-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
		Subsystem clock (fSUB) operation		2.4 V ≤ VDD ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
External system clock frequency	fex	2.7 V ≤ VDD ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ VDD ≤ 2.7 V			1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input high-level width, low-level width	texH,	2.7 V ≤ VDD ≤ 5.5 V			24			ns
	texL	2.4 V ≤ VDD ≤ 2.7 V			30			ns
	texHS, texLS				13.7			μs
Ti00 to Ti03, Ti10 to Ti13 input high-level width, low-level width	tTiH, tTiL				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	100			ns
				2.4 V ≤ EVDD0 < 2.7 V	300			ns
Timer RJ input high-level width, low-level width	tTjIH, tTjIL	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	40			ns
				2.4 V ≤ EVDD0 < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when $\text{EVDD0} < \text{VDD}$
 $2.4\text{ V} \leq \text{EVDD0} < 2.7\text{ V}$: MIN. 125 ns

Remark fMCK: Timer array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

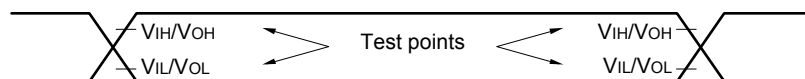
(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tTDIH, tTDIL	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/fCLK			ns
Timer RD forced cutoff signal input low-level width	tTDSIL	P130/INTP0	2MHz < fCLK ≤ 32 MHz	1			μs
			fCLK ≤ 2 MHz	1/fCLK + 1			
Timer RG input high-level width, low-level width	tTGIH, tTGIL	TRGIOA, TRGIOB		2.5/fCLK			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	fTO	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output frequency	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
Interrupt input high-level width, low-level width	tINTH, tINTL	INTP0	2.4 V ≤ VDD ≤ 5.5 V	1			μs
		INTP1 to INTP11	2.4 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level width	tKR	KR0 to KR7	2.4 V ≤ EVDD0 ≤ 5.5 V	250			ns
RESET low-level width	tRSL			10			μs

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq E_{VDD0} = E_{VDD1} \leq 5.5\text{ V}$, $V_{SS} = E_{VSS0} = E_{VSS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1		$2.4\text{ V} \leq E_{VDD0} \leq 5.5\text{ V}$		$f_{MCK}/12$ Note 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when $FRQSEL4 = 1$.

Note 2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

$2.4\text{ V} \leq E_{VDD0} < 2.7\text{ V}$: MAX. 1.3 Mbps

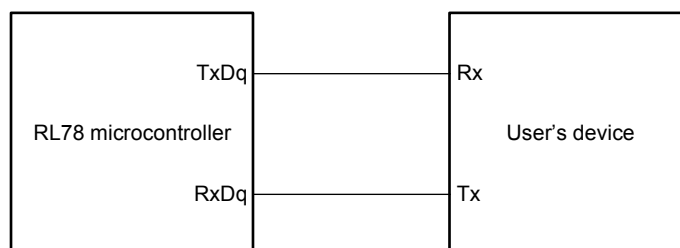
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 32 MHz ($2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$)

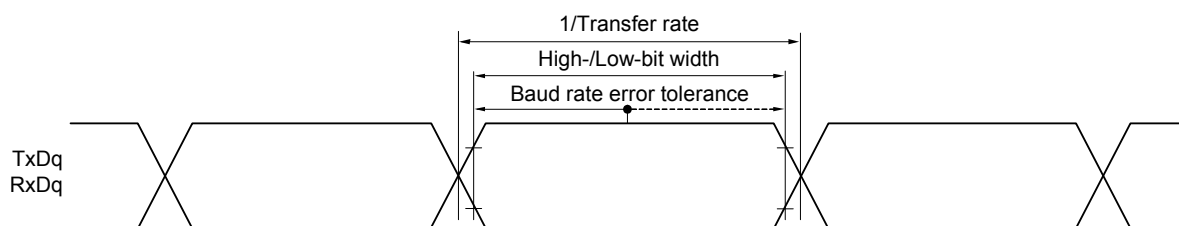
16 MHz ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)

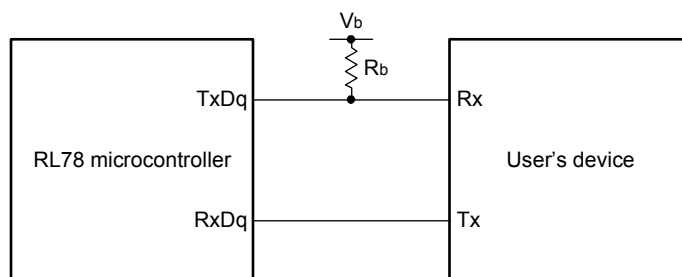
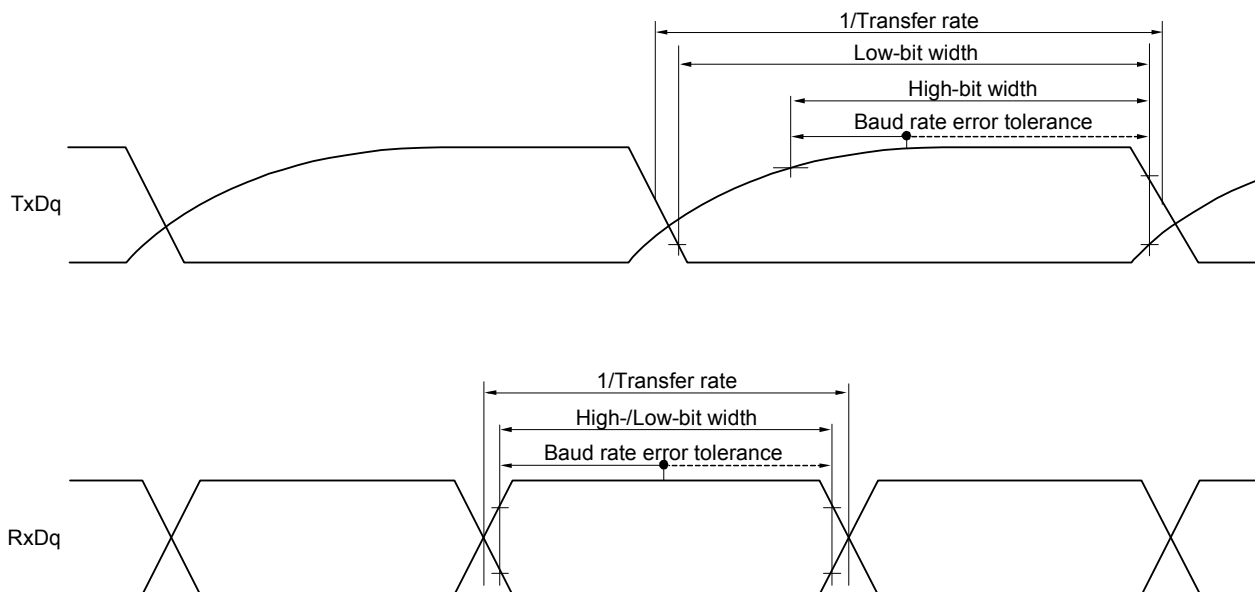


Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

UART mode connection diagram (during communication at different potential)**UART mode bit width (during communication at different potential) (reference)**

Remark 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

$C_b[\text{F}]$: Communication line (TxDq) load capacitance, $V_b[\text{V}]$: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

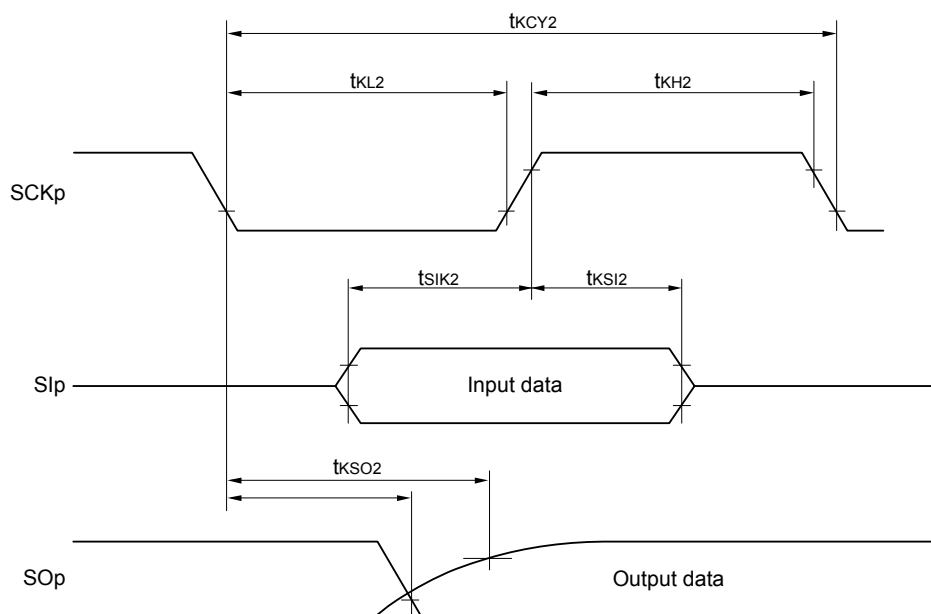
Remark 3. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

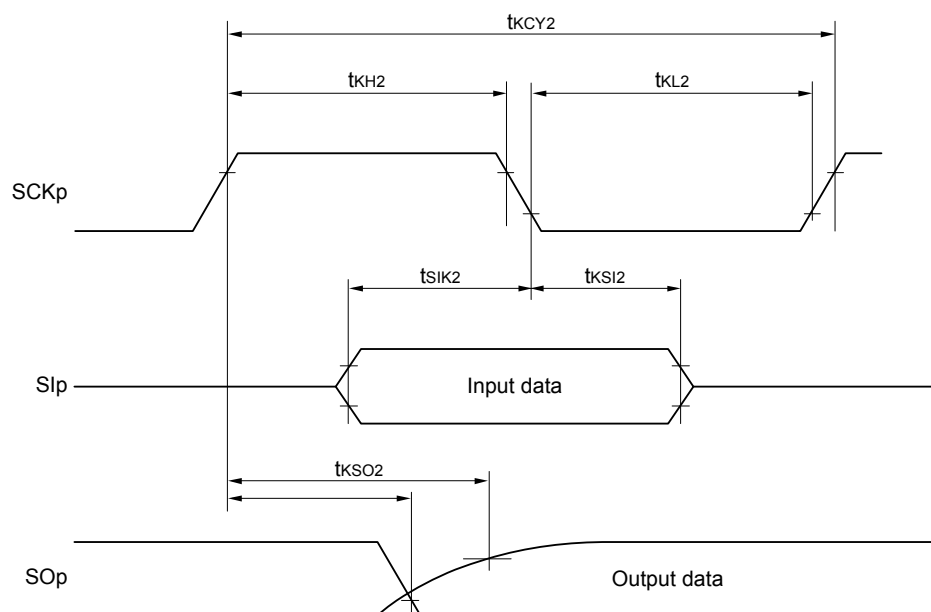
m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



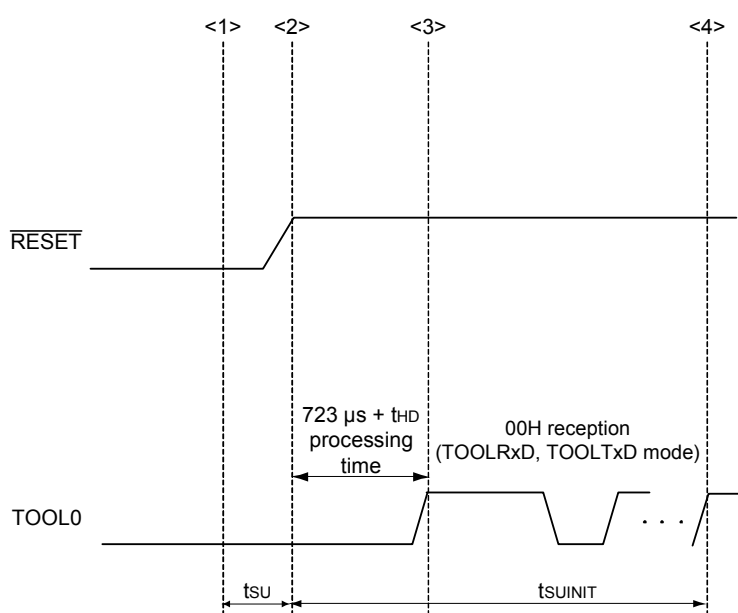
Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

3.10 Timing of Entry to Flash Memory Programming Modes

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

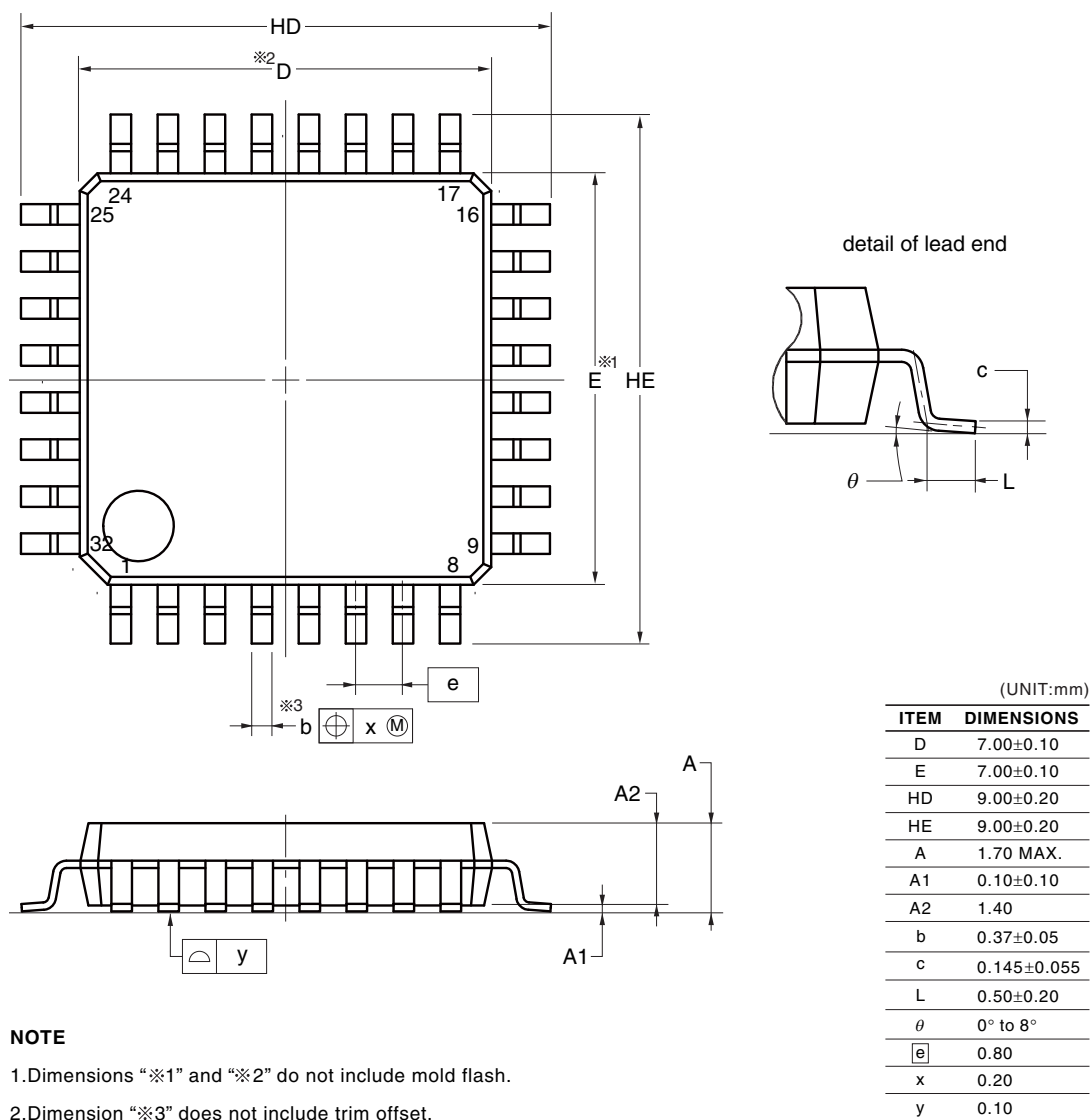
Remark t_{SUINIT} : The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

t_{SU} : How long from when the TOOL0 pin is placed at the low level until a pin reset ends

t_{HD} : How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP
 R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP
 R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2

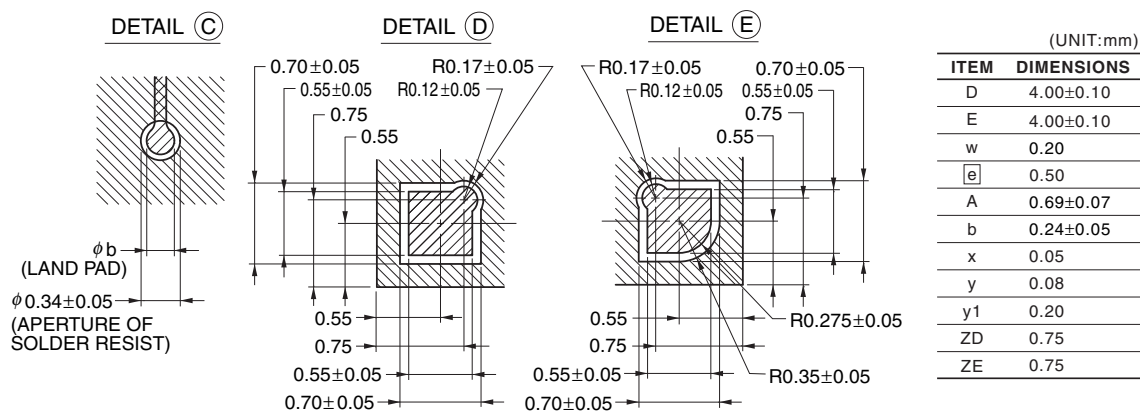
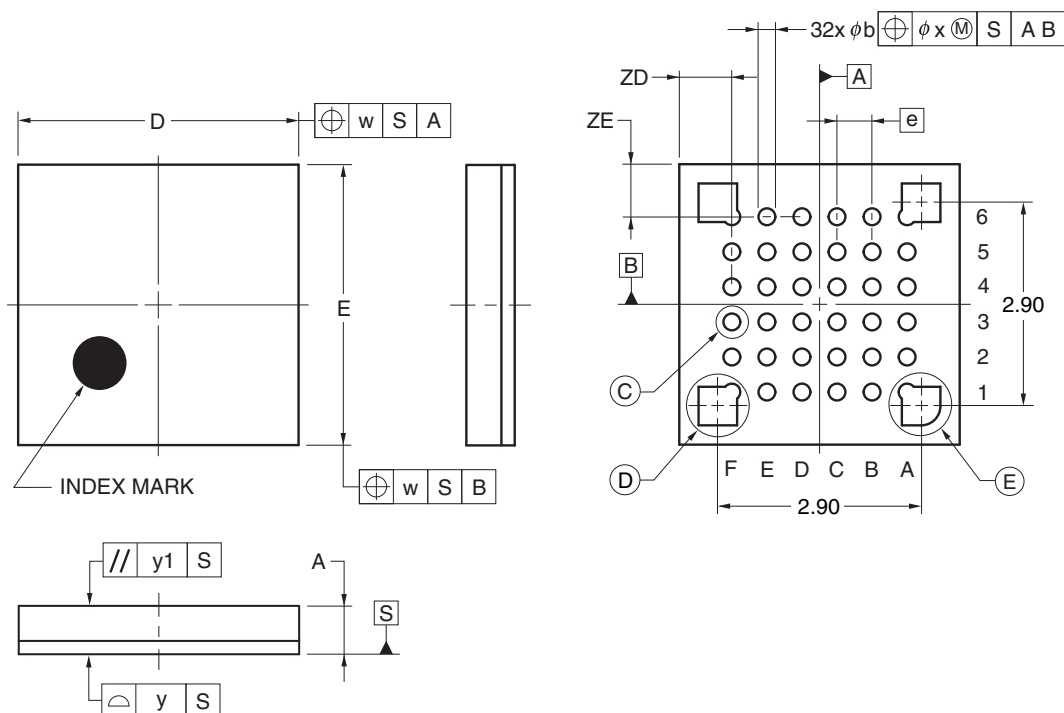


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4.3 36-pin products

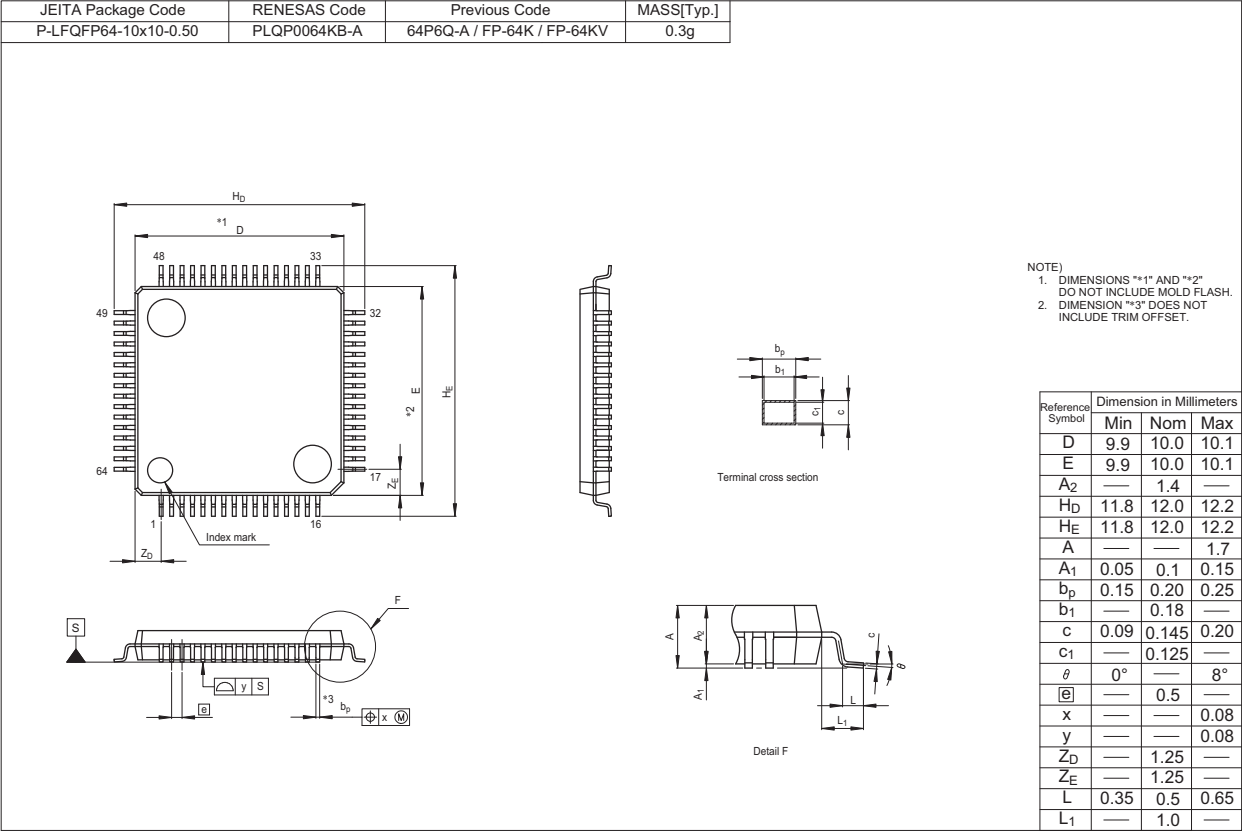
R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



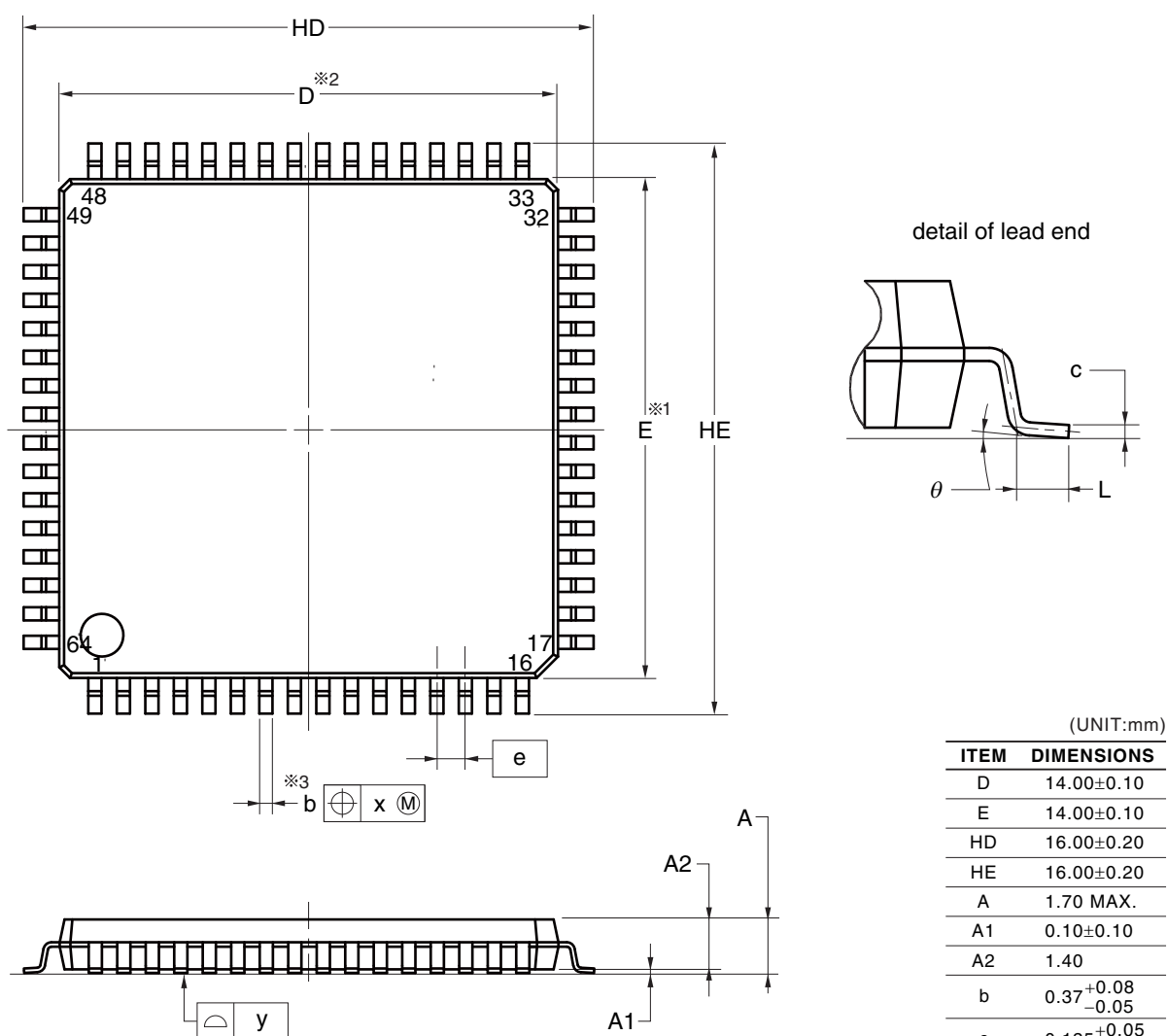
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R5F104LKAFB, R5F104LLAFB
R5F104LKGFB, R5F104LLGFB



R5F104LCAFP, R5F104LDAFP, R5F104LEAFP, R5F104LFAFP, R5F104LGAFP, R5F104LHAFP, R5F104LJAFP
 R5F104LCDFP, R5F104LDDFP, R5F104LEDFP, R5F104LDFP, R5F104LGDFP, R5F104LHDFP, R5F104LJDFP
 R5F104LCGFP, R5F104LDGFP, R5F104LEGFP, R5F104LFGFP, R5F104LGGFP, R5F104LHGFP, R5F104LJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-14x14-0.80	PLQP0064GA-A	P64GC-80-GBW-1	0.7



NOTE

1. Dimensions "※1" and "※2" do not include mold flash.
2. Dimension "※3" does not include trim offset.

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